

# **isc Silicon NPN Power Transistor**

**MJL4281A** 

### **DESCRIPTION**

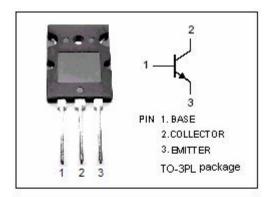
- · High Collector-Emitter Breakdown Voltage
  - : V<sub>(BR)CEO</sub>= 350V(Min)
- High DC Current Gain
  - :h<sub>FE</sub> = 25 Min @ IC = 8 Adc
- Complement to Type MJL4302A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

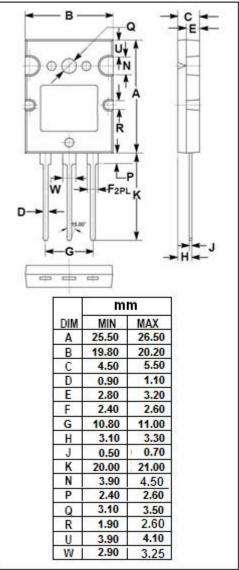
## **APPLICATIONS**

- Perforated Emitter technology
- High power audio output, disk head positioners linear applications

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>СВО</sub>	Collector-Base Voltage	350	V
V <sub>CEO</sub>	Collector-Emitter Voltage	350	V
V <sub>EBO</sub>	Emitter-Base Voltage 5.0		V
lc	Collector Current-Continuous	15	Α
I <sub>B</sub>	Base Current-Continuous	1.5	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	230	W
s://www.	Junction Temperature	150	$^{\circ}\mathbb{C}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C





isc website: www.iscsemi.com

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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS Sheet. CO	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= 50mA; I <sub>B</sub> = 0	350		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8.0A; I <sub>B</sub> = 0.8A		1.0	V
V <sub>BE(sat)</sub>	Emitter-Base Saturation Voltage	I <sub>C</sub> = 8.0A; I <sub>B</sub> = 0.8A		1.4	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V		1.5	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 200V; I <sub>E</sub> = 0		100	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		5.0	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	80	250	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	80	250	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	80	250	
h <sub>FE-4</sub>	DC Current Gain	Ic= 5A; VcE= 5V	80	250	
h <sub>FE-5</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	50		
h <sub>FE-6</sub>	DC Current Gain	I <sub>C</sub> = 15A; V <sub>CE</sub> = 5V	10		

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